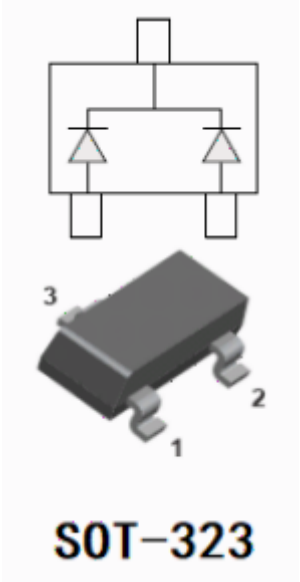




6 P D O O 6 L J Q D O) D V W 6 Z L W F K L Q J ' L R



-) H D W X U H V
- z Moisture sensitivity level 1
 - ° Reverse voltage 100V
 - ° Average forward current
single diode loaded 215mA
double diode loaded 125mA

- \$ S S O L F D W L R Q
- z Signal switching
 - ° High frequency rectifier

- 0 H F K D Q L F D O G D W D
- z 3 D F N D J S O T - 3 2 3
 - ° 7 H U P L Q D D M Mated leads, solderable per J-STD-002 and JESD22-B102

■ 0 D [L P X P 5 D W = 2 5 V (Unless otherwise specified)

3 D U D P H W H U	6 \ P E R O	8 Q L W	9 D O X H
Device marking code			JX
Repetitive peak reverse voltage	V _{RRM}	V	100
Forward current @ double diode loaded	I _F	mA	215
			125

Non-repetitive surge peak forward current @ t=8.3ms half-sine wave

} Non-repetitive sur

I_{AFS}

Power dissipation	P _D	mW	200
Junction temperature	T _J	°C	-55 to +150
Storage temperature	T _{STG}	°C	-55 to +150



BAV170WT

RoHS
COMPLIANT

■ (OHFWULFDO & KDUDFWHULVWLFLV (unless otherwise specified))

3DUDPHWHU	6\PERO	8QLW	&RQGLWLRQ	0LQ	7\S	0D[
Reverse voltage	V_R	V	$I_R=100\mu A$	100		
Forward voltage	V_{F1}	V	$I_F=1mA$			0.9
	V_{F2}	V	$I_F=10mA$			1.0
	V_{F3}	V	$I_F=50mA$			1.1
	V_{F4}	V	$I_F=150mA$			1.25
Reverse leakage current	I_R	nA	$V_R=75V$			5
Junction capacitance	C_j	pF	$V_R=0V, f=1MHz$			4
Reverse recovery time	T_{rr}	us	$I_F=I_R=10mA$ $I_{rr}=0.1 \cdot I_R$, $R_L=100\Omega$			3

■ 7KHUPDO & KDUDFWHULVWLFLV

3\$5\$0(7(5	6\PERO	8QLW	9DOXH
Thermal resistance, junction-to-ambient	$R_{\theta J-A}^{(1)}$	$\frac{^{\circ}C}{W}$	625
Thermal resistance, junction-to-case	$R_{\theta J-C}^{(1)}$	$\frac{^{\circ}C}{W}$	500

Note:

- 1 Device mounted on PCB, single-sided copper with standard footprint



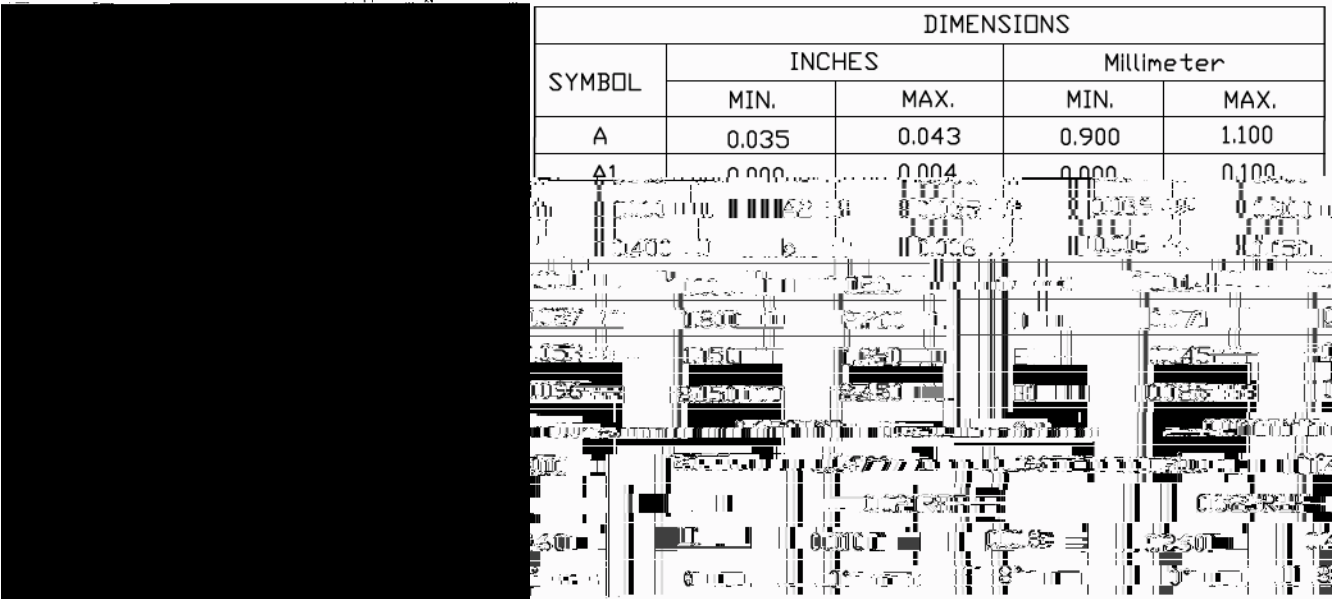
BAV170WT

RoHS
COMPLIANT

■ 2UGHULQJ ,QIRUPDWLRQ

3UHIHUHG	3DFNL FRGH	8QLW ZHLJ	0LQLPXP SDFNDJH	,QQHU ER TXDQWLW\	2XWHU FDU TXDQWLW\	'HOLYHU\ PRGH
BAV170WT	F2	Approximate 0.005	3000	30000	120000	7" reel

■ 2XWOLQH 'LPHQVLRQV



■ 6XJJHVWHG 3DG /D\RXW

